

MOSFET – P-Channel, POWERTRENCH®

60 V

FDD5614P

General Description

This 60 V P-Channel MOSFET uses onsemi's high voltage POWERTRENCH process. It has been optimized for power management applications.

Features

- -15 A , -60 V
 - ◆ $R_{DS(ON)} = 100\text{ m}\Omega$ at $V_{GS} = -10\text{ V}$
 - ◆ $R_{DS(ON)} = 130\text{ m}\Omega$ at $V_{GS} = -4.5\text{ V}$
- Fast Switching Speed
- High Performance Trench Technology for Extremely Low $R_{DS(ON)}$
- High Power and Current Handling Capability
- This is a Pb-Free Device

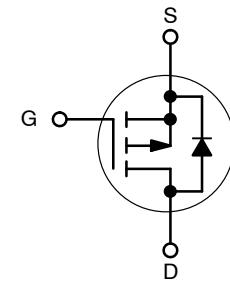
Applications

- DC/DC Converter
- Power Management
- Load Switch

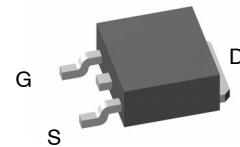
ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Ratings	Unit
V _{DSS}	Drain-Source Voltage	-60	V
V _{GSS}	Gate-Source Voltage	± 20	V
I _D	Drain Current – Continuous (Note 3) – Pulsed (Note 1a)	-15 -45	A
P _D	Power Dissipation for Single Operation (Note 1) (Note 1a) (Note 1b)	42 3.8 1.6	W
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



P-Channel MOSFET

DPAK3 (TO-252 3 LD)
CASE 369AS

MARKING DIAGRAM



FDD5614P = Specific Device Code
\$Y = onsemi Logo
&Z = Assembly Plant Code
&3 = 3-Digit Date Code
&K = 2-Digits Lot Run Traceability Code

ORDERING INFORMATION

Device	Package	Shipping [†]
FDD5614P	TO-252-3 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case (Note 1)	3.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	40	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1b)	96	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
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DRAIN-SOURCE AVALANCHE RATINGS (Note 1)

W_{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = -30\text{ V}$, $I_D = -4.5\text{ A}$	–	–	90	mJ
I_{AR}	Maximum Drain-Source Avalanche Current		–	–	-4.5	A

OFF CHARACTERISTICS

V_{VDSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$	-60	–	–	V
$\frac{\Delta V_{GS(\text{th})}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, Referenced to 25°C	–	-49	–	$\text{mV/}^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -48\text{ V}$, $V_{GS} = 0\text{ V}$	–	–	-1	μA
I_{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 20\text{ V}$, $V_{DS} = 0\text{ V}$	–	–	100	nA
I_{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -20\text{ V}$, $V_{DS} = 0\text{ V}$	–	–	-100	nA

ON CHARACTERISTICS (Note 2)

$V_{GS(\text{th})}$	Gate to Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	-1	-1.6	-3	V
$\frac{\Delta V_{GS(\text{th})}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\text{ }\mu\text{A}$, Referenced to 25°C	–	4	–	$\text{mV/}^\circ\text{C}$
$R_{DS(\text{on})}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}$, $I_D = -4.5\text{ A}$	–	76	100	$\text{m}\Omega$
		$V_{GS} = -4.5\text{ V}$, $I_D = -3.9\text{ A}$	–	99	130	
		$V_{GS} = -10\text{ V}$, $I_D = -4.5\text{ A}$, $T_J = 125^\circ\text{C}$	–	137	185	
$I_{D(\text{on})}$	On-State Drain Current	$V_{GS} = -10\text{ V}$, $V_{DS} = -5\text{ V}$	-20	–	–	A
g_{FS}	Forward Transconductance	$V_{DS} = -5\text{ V}$, $I_D = -3\text{ A}$	–	8	–	S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = -30\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	–	759	–	pF
C_{oss}	Output Capacitance		–	90	–	pF
C_{rss}	Reverse Transfer Capacitance		–	39	–	pF

SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -30\text{ V}$, $I_D = -1\text{ A}$, $V_{GS} = -10\text{ V}$, $R_{\text{GEN}} = 6\text{ }\Omega$	–	7	14	ns
t_r	Turn-On Rise Time		–	10	20	ns
$t_{d(off)}$	Turn-Off Delay Time		–	19	34	ns
t_f	Turn-Off Fall Time		–	12	22	ns
Q_g	Total Gate Charge	$V_{DS} = -30\text{ V}$, $I_D = -4.5\text{ A}$, $V_{GS} = -10\text{ V}$	–	15	24	nC
Q_{gs}	Gate-Source Charge		–	2.5	–	nC
Q_{gd}	Gate-Drain Charge		–	3.0	–	nC

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (continued)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
DRAIN-SOURCE AVELANCHE RATINGS						
I_S	Maximum Continuous Drain-Source Diode Forward Current		-	-	-3.2	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}$, $I_S = -3.2 \text{ A}$ (Note 2)	-	-0.8	-1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) $R_{\theta JA} = 40^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper.

b) $R_{\theta JA} = 96^\circ\text{C}/\text{W}$ when mounted on a minimum pad.



2. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%.

3. Maximum current is calculated as:
$$\sqrt{\frac{P_D}{R_{DS(ON)}}}$$

where P_D is maximum power dissipation at $T_C = 25^\circ\text{C}$ and $R_{DS(ON)}$ is at $T_{J(\text{max})}$ and $V_{GS} = 10 \text{ V}$. Package current limitation is 21 A.

TYPICAL CHARACTERISTICS

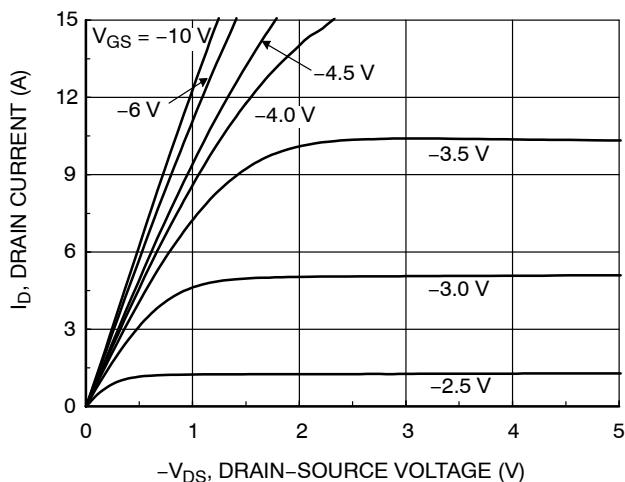


Figure 1. On-Region Characteristics

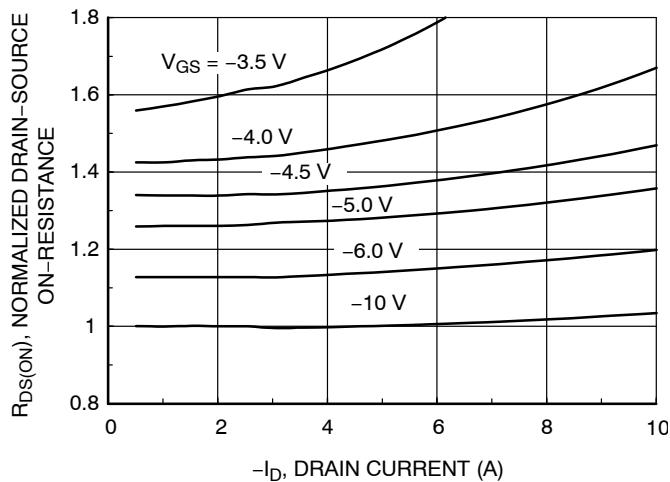


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

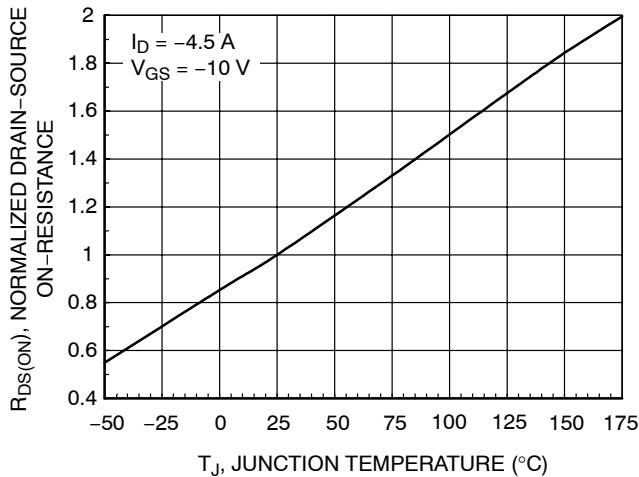


Figure 3. On-Resistance Variation with Temperature

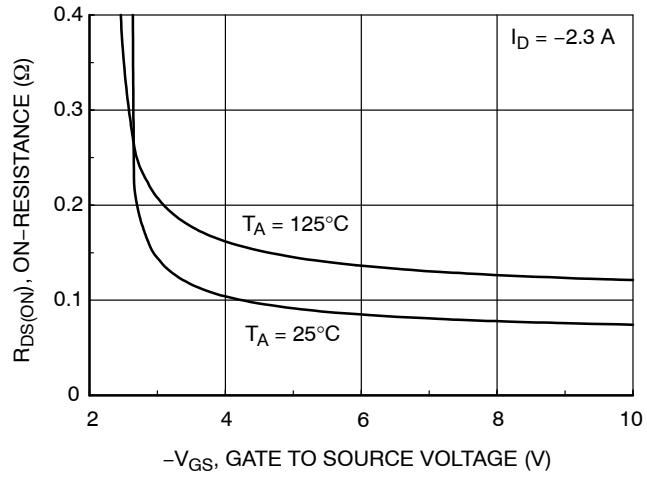


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

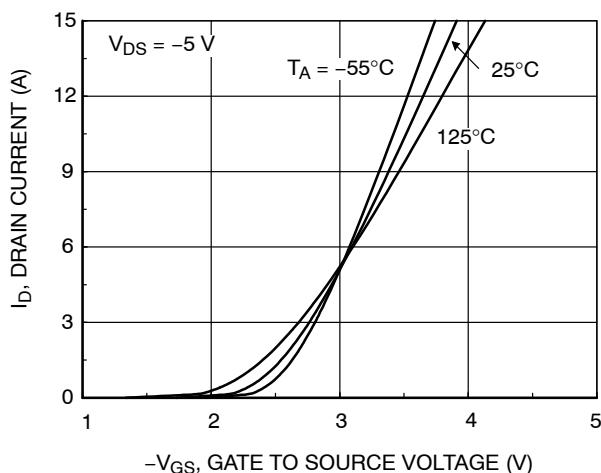


Figure 5. Transfer Characteristics

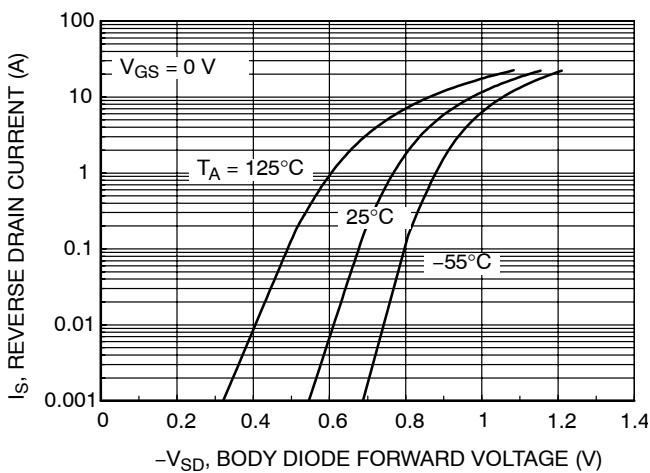


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

TYPICAL CHARACTERISTICS (continued)

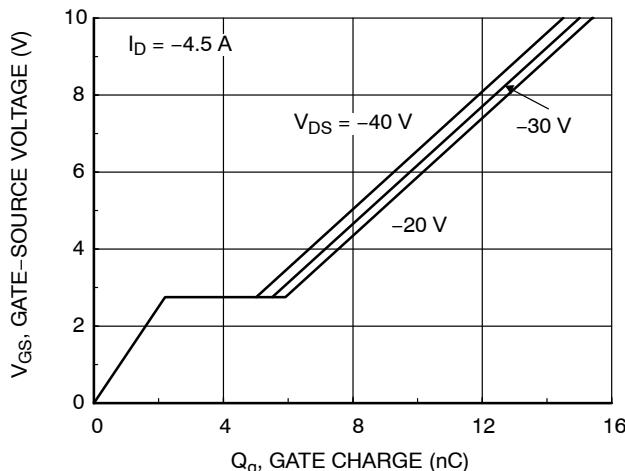


Figure 7. Gate Charge Characteristics

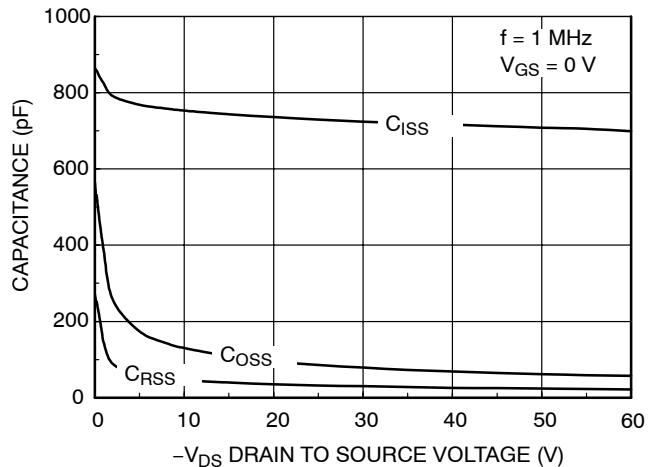


Figure 8. Capacitance Characteristics

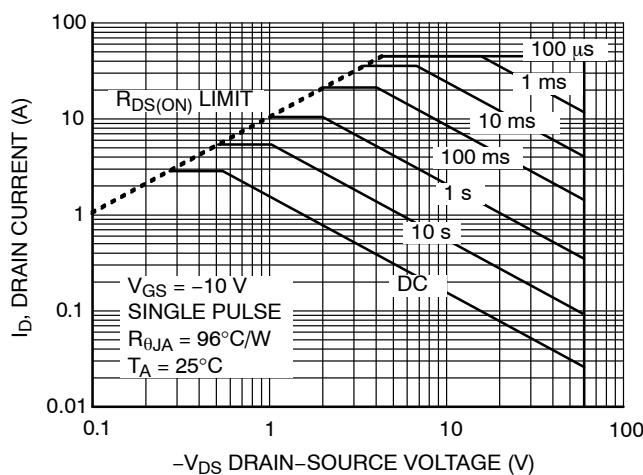


Figure 9. Maximum Safe Operating Area

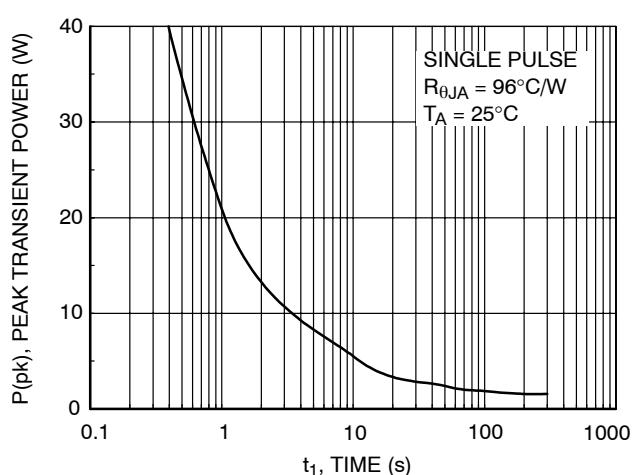
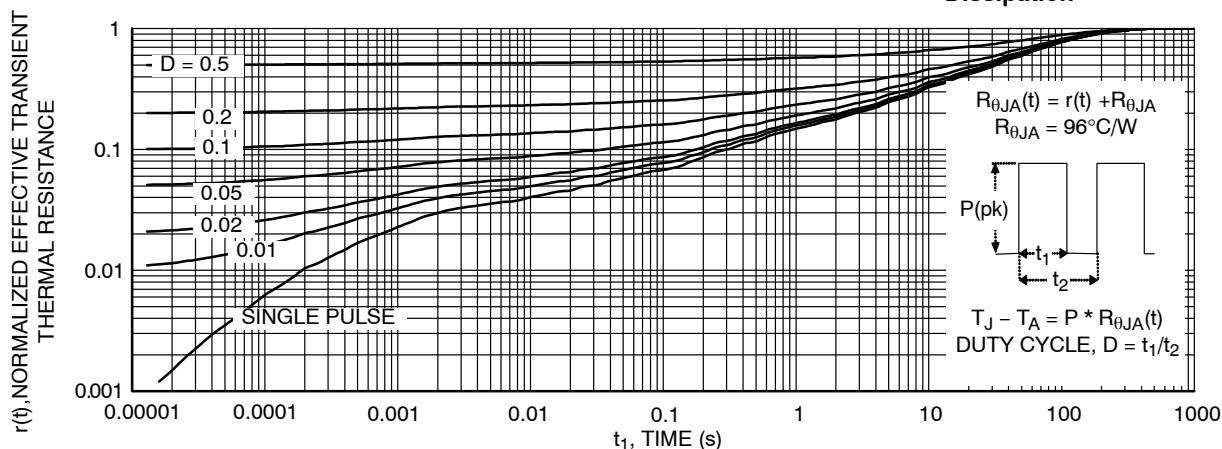


Figure 10. Single Pulse Maximum Power Dissipation

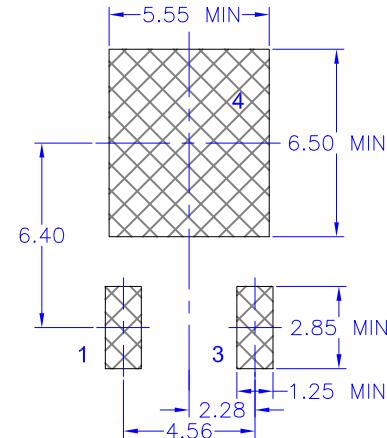
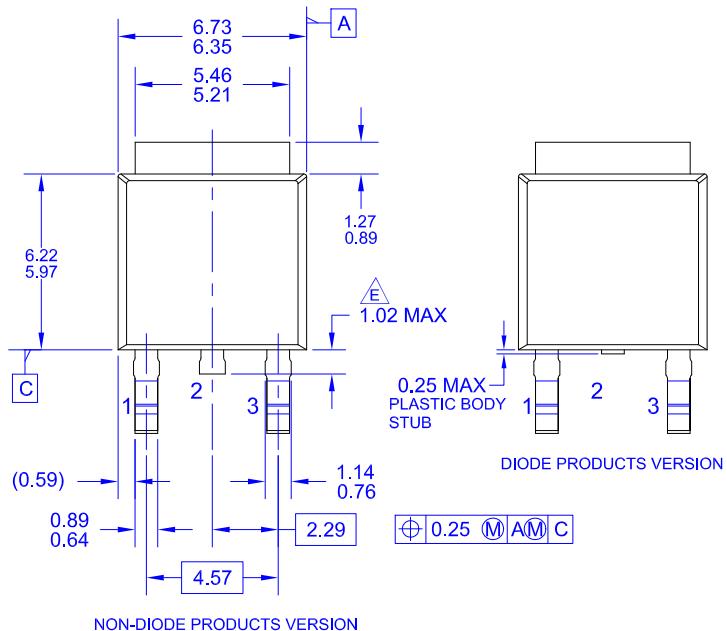


Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

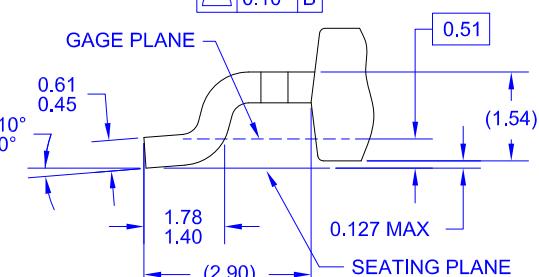
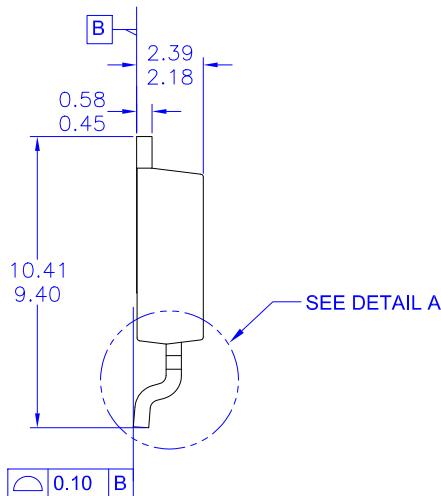
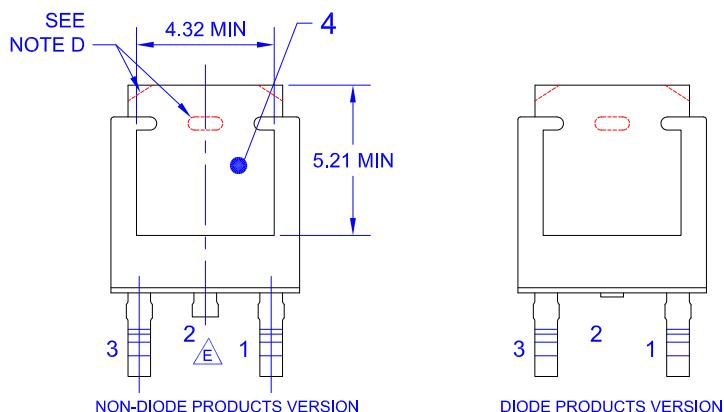
Figure 11. Transient Thermal Response Curve

DPAK3 (TO-252 3 LD)
CASE 369AS
ISSUE O

DATE 30 SEP 2016



LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED
A) THIS PACKAGE CONFORMS TO JEDEC, TO-252,
ISSUE C, VARIATION AA.

B) ALL DIMENSIONS ARE IN MILLIMETERS.

C) DIMENSIONING AND TOLERANCING PER
ASME Y14.5M-2009.

D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED
CORNERS OR EDGE PROTRUSION.

E) TRIMMED CENTER LEAD IS PRESENT ONLY FOR DIODE PRODUCTS

F) DIMENSIONS ARE EXCLUSIVE OF BURRS,
MOLD FLASH AND TIE BAR EXTRUSIONS.

G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD
TO228P991X239-3N.

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